# **General Purpose NPN Amplifier Transistor**

### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant\*

## **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	60	Vdc
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	7.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	500	mAdc
Collector Current – Peak	I <sub>C(P)</sub>	1.0	Adc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P <sub>D</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	−55 ~ <b>+</b> 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

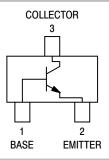


## ON Semiconductor®

http://onsemi.com



SC-59 CASE 318D STYLE 1



## **MARKING DIAGRAM**



WR = Specific Device Code

M = Date Code

■ = Pb–Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MSD-602RT1G	SC-59 (Pb-Free)	3,000 / Tape & Reel
SMSD-602RT1G	SC-59 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** $(T_A = 25^{\circ}C)$

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	_	V
Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)</sub> CBO	60	_	V
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu A, I_C = 0$ )	V <sub>(BR)EBO</sub>	7.0	_	V
Collector–Base Cutoff Current (V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	0.1	μΑ
DC Current Gain (Note 1) (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 150 mA) (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 500 mA)	h <sub>FE1</sub> h <sub>FE2</sub>	120 40	240 -	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 300 mA, I <sub>B</sub> = 30 mA)	V <sub>CE(sat)</sub>	-	0.6	V
Base–Emitter On Voltage (I <sub>C</sub> = 300 mA, V <sub>CE</sub> = 5 V)	V <sub>BE(on)</sub>	-	1.0	V
Base–Emitter Saturation Voltage (I <sub>C</sub> = 300 mA, I <sub>B</sub> = 30 mA)	V <sub>BE(sat)</sub>	_	1.0	V
Output Capacitance (V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width  $\leq 300 \, \mu s$ , D.C.  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS

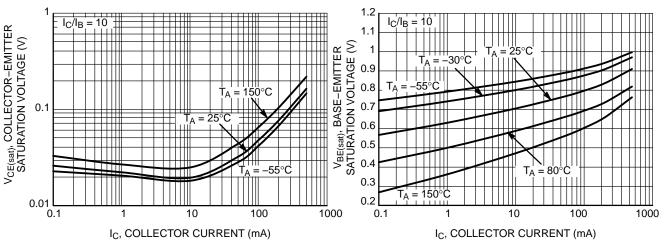


Figure 1. Collector-Emitter Saturation Voltage vs. Collector Current

Figure 2. Base-Emitter Saturation Voltage vs. **Collector Current** 

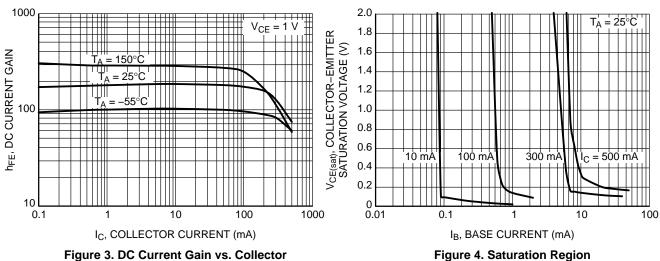


Figure 3. DC Current Gain vs. Collector Current

1.0 100 V<sub>BE(on)</sub>, BASE-EMITTER VOLTAGE (V) -30<sup>o</sup>€ C<sub>ibo</sub> 0.9 0.8 CAPACITANCE (pF) 0.7  $C_{obo}$ 0.6 10 = 80°C 0.5 0.3  $V_{CE} = 5 V$ 0.2 1000 0.1 100 I<sub>C</sub>, COLLECTOR CURRENT (mA) V<sub>R</sub>, REVERSE VOLTAGE (V)

Figure 5. Base-Emitter Turn-On Voltage vs. **Collector Current** 

Figure 6. Capacitance

## **TYPICAL CHARACTERISTICS**

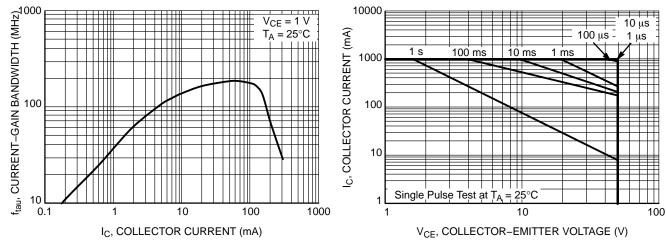


Figure 7. Current Gain Bandwidth Product vs.
Collector Current

Figure 8. Safe Operating Area

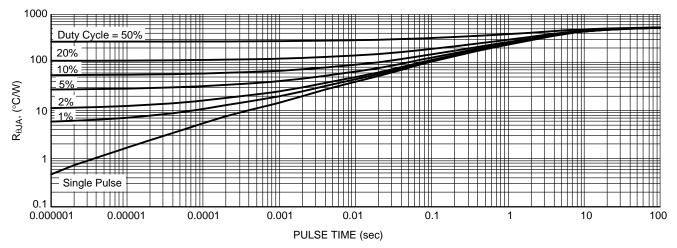


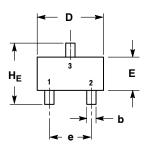
Figure 9. Thermal Response

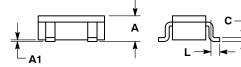




SC-59 CASE 318D-04 ISSUE H

**DATE 28 JUN 2012** 





## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code М

= Pb-Free Package\*

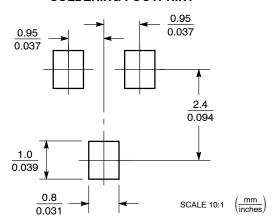
(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
Е	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

## **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. CATHODE	PIN 1. ANODE
2. N.C.	2. CATHODE	2. CATHODE
3. ANODE	3. ANODE	3. ANODE/CATHODE

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